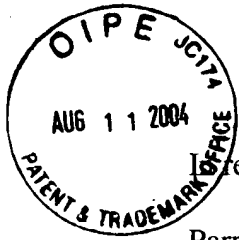


FILED 2125
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of :
Parris C.M. HAWKINS et al. :
Serial No. 09/800,980 : Group Art Unit: 2125
Filed: March 8, 2001 : Examiner: Sean P. Shechtman
For: DYNAMIC AND EXTENSIBLE TASK GUIDE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This submission does not constitute a representation that a search has been made or that no better art exists and does not constitute an admission or representation that any of the listed documents is material or constitutes prior art. If it should be determined that any of the listed documents does not constitute prior art under the United States law, Applicants reserve the right

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to present to the Office the relevant facts and law regarding the appropriate status of such document.

Please charge the fee of \$180.00 under 37 CFR 1.17(p) to Deposit Account No. 08-0219. The Commissioner is authorized to charge any deficiency in any fees pursuant to 37 CFR § 1.17 associated with this communication and to credit any excess payment to Deposit Account No. 08-0219.

Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 005198 USA/ Consilium/Consilium		SERIAL NO. 09/800,980	
				APPLICANT Parris C.M. HAWKINS et al.			
				FILING DATE March 8, 2001		GROUP 2125	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
	4,957,605	09/18/90	Hurwitt et al.			04/17/89	
	5,240,552	08/31/93	Yu et al.			12/11/91	
	5,369,544	11/29/94	Mastrangelo			04/05/93	
	5,665,214	09/09/97	Iturralde			05/03/95	
	5,695,810	12/09/97	Dubin et al.			11/20/96	
	5,824,599	10/20/98	Schacham-Diamand et al.			01/16/96	
	5,831,851	11/03/98	Eastburn et al.			03/21/95	
	5,838,951	11/17/98	Song			08/28/96	
	5,859,777	01/12/99	Yokoyama et al.			05/13/97	
	5,871,805	02/16/99	Lemelson			04/08/96	
	5,943,550	08/24/99	Fulford, Jr. et al.			03/29/96	
	6,037,664	03/14/00	Zhao et al.			03/31/98	
	6,059,636	05/09/00	Inaba et al.			07/09/98	
	6,096,649	08/01/00	Jang			10/25/99	
	6,100,195	08/08/00	Chan et al.			12/28/98	
	6,114,238	09/05/00	Liao			05/20/98	
	6,150,270	11/21/00	Matsuda et al.			01/07/99	
	6,181,013 B1	01/30/01	Liu et al.			03/13/00	
	6,212,961 B1	04/10/01	Dvir			02/11/99	
	6,226,563 B1	05/01/01	Lim			09/04/98	
	6,228,280 B1	05/08/01	Li et al.			05/06/98	
	6,237,050 B1	05/22/01	Kim et al.			09/04/98	
	2001/0006873 A1	07/05/01	Moore			02/13/01	
	6,259,160 B1	07/10/01	Lopatin et al.			04/21/99	
	6,281,127 B1	08/28/01	Shue			04/15/99	
EXAMINER				DATE CONSIDERED			

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March 8, 2001

GROUP
2125

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	6,339,727 B1	01/15/02	Ladd			12/21/98
	6,355,559 B1	03/12/02	Havemann et al.			11/03/00
	6,391,780 B1	05/21/02	Shih et al.			08/23/99
	6,417,014 B1	07/09/02	Lam et al.			10/19/99
	6,427,093 B1	07/30/02	Toprac			10/07/99
	6,432,728 B1	08/13/02	Tai et al.			10/16/00
	6,449,524 B1	09/10/02	Miller et al.			01/04/00
	6,455,415 B1	09/24/02	Lopatin et al.			04/16/01
	2002/0165636 A1	11/07/02	Hasan			04/24/02
	6,484,064 B1	11/19/02	Campbell			10/05/99
	6,495,452 B1	12/17/02	Shih			08/18/99
	2002/0193899 A1	12/19/02	Shanmugasundram et al.			05/01/02
	2003/0017256 A1	01/23/03	Shimane			06/12/02
	6,515,368 B1	02/04/03	Lopatin et al.			12/07/01
	6,517,414 B1	02/11/03	Tobin et al.			03/10/00
	6,528,409 B1	03/04/03	Lopatin et al.			04/29/02
	6,537,912 B1	03/25/03	Agarwal			08/25/00
	6,580,958 B1	06/17/03	Takano			11/22/99
	6,605,549 B2	08/12/03	Leu et al.			09/29/01
	6,607,976 B2	08/19/03	Chen et al.			09/25/01
	6,609,946 B1	08/26/03	Tran			07/14/00
	6,616,513 B1	09/09/03	Osterheld			04/05/01
	6,624,075 B1	09/23/03	Lopatin et al.			11/05/02
	6,630,741 B1	10/07/03	Lopatin et al.			12/07/01
	6,660,633 B1	12/09/03	Lopatin et al.			02/26/02
	6,708,074 B1	03/16/04	Chi et al.			08/11/00
	6,708,075 B2	03/16/04	Sonderman et al.			11/16/01
	6,728,587 B2	04/27/04	Goldman et al.			12/27/00

EXAMINER

DATE CONSIDERED

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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
	EP 0 932 195 A1	07/28/99	EP			X	
	EP 1 083 470 A2	03/14/01	EP			X	
	GB 2 365 215 A	02/13/02	GB			X	

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	Sun, S.C. 1998. "CVD and PVD Transition Metal Nitrides as Diffusion Barriers for Cu Metallization." <i>IEEE</i> . pp. 243-246.
	Tagami, M., A. Furuya, T. Onodera, and Y. Hayashi. 1999. "Layered Ta-nitrides (LTN) Barrier Film by Power Swing Sputtering (PSS) Technique for MOCVD-Cu Damascene Interconnects." <i>IEEE</i> . pp. 635-638.
	Yamagishi, H., Z. Tokei, G.P. Beyer, R. Donaton, H. Bender, T. Nogami, and K. Maex. 2000. "TEM/SEM Investigation and Electrical Evaluation of a Bottomless I-PVD TA(N) Barrier in Dual Damascene" (Abstract). <i>Advanced Metallization Conference 2000</i> . San Diego, CA.
	Eisenbraun, Eric, Oscar van der Straten, Yu Zhu, Katharine Dovidenko, and Alain Kaloyeros. 2001. "Atomic Layer Deposition (ALD) of Tantalum-Based Materials for Zero Thickness Copper Barrier Applications" (Abstract). <i>IEEE</i> . pp. 207-209.
	Smith, S.R., K.E. Elers, T. Jacobs, V. Blaschke, and K. Pfeifer. 2001. "Physical and Electrical Characterization of ALD Tin Used as a Copper Diffusion Barrier in 0.25 μ m, Dual Damascene Backend Structures" (Abstract). <i>Advanced Metallization Conference 2001</i> . Montreal, Quebec.
	Kim, Y.T. and H. Sim. 2002. "Characteristics of Pulse Plasma Enhanced Atomic Layer Deposition of Tungsten Nitride Diffusion Barrier for Copper Interconnect" (Abstract). <i>IEIC Technical Report</i> . Vol. 102, No. 178, pp. 115-118.
	Elers, Kai-Erik, Ville Saanila, Pekka J. Soininen, Wei-Min Li, Juhana T. Kostamo, Suvi Haukka, Jyrki Juhanoja, and Wim F.A. Besling. 2002. "Diffusion Barrier Deposition on a Copper Surface by Atomic Layer Deposition" (Abstract). <i>Advanced Materials</i> . Vol. 14, No. 13-14, pp. 149-153.
	Peng, C.H., C.H. Hsieh, C.L. Huang, J.C. Lin, M.H. Tsai, M.W. Lin, C.L. Chang, Winston S. Shue, and M.S. Liang. 2002. "A 90nm Generation Copper Dual Damascene Technology with ALD TaN Barrier." <i>IEEE</i> . pp. 603-606.
	Van der Straten, O., Y. Zhu, E. Eisenbraun, and A. Kaloyeros. 2002. "Thermal and Electrical Barrier Performance Testing of Ultrathin Atomic Layer Deposition Tantalum-Based Materials for Nanoscale Copper Metallization." <i>IEEE</i> . pp. 188-190.
	Wu, Z.C., Y.C. Lu, C.C. Chiang, M.C. Chen, B.T. Chen, G.J. Wang, Y.T. Chen, J.L. Huang, S.M. Jang, and M.S. Liang. 2002. "Advanced Metal Barrier Free Cu Damascene Interconnects with PECVD Silicon Carbide Barriers for 90/65-nm BEOL Technology." <i>IEEE</i> . pp. 595-598.
	July 25, 2003. International Search Report for PCT/US02/24858.
	March 30, 2004. Written Opinion for PCT/US02/19062.
	April 9, 2004. Written Opinion for PCT/US02/19116.
	April 22, 2004. Office Action for U.S. Serial No. 09/998,372, filed November 30, 2001.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

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